

Interview Summary	Application No.	Applicant(s)
	09/428,052	IRINO, KIYOSHI
	Examiner	Art Unit
	José R. Díaz	2815

All participants (applicant, applicant's representative, PTO personnel):

(1) José R. Díaz. (3) _____.

(2) Stephen Adrian. (4) _____.

Date of Interview: 02 December 2004.

Type: a) Telephonic b) Video Conference
c) Personal [copy given to: 1) applicant 2) applicant's representative]

Exhibit shown or demonstration conducted: d) Yes e) No.
If Yes, brief description: _____.

Claim(s) discussed: 6, 10 and 15.

Identification of prior art discussed: Ito et al.; Wristers et al.; and Duane.

Agreement with respect to the claims f) was reached. g) was not reached. h) N/A.

Substance of Interview including description of the general nature of what was agreed to if an agreement was reached, or any other comments: See Continuation Sheet.

(A fuller description, if necessary, and a copy of the amendments which the examiner agreed would render the claims allowable, if available, must be attached. Also, where no copy of the amendments that would render the claims allowable is available, a summary thereof must be attached.)

THE FORMAL WRITTEN REPLY TO THE LAST OFFICE ACTION MUST INCLUDE THE SUBSTANCE OF THE INTERVIEW. (See MPEP Section 713.04). If a reply to the last Office action has already been filed, APPLICANT IS GIVEN ONE MONTH FROM THIS INTERVIEW DATE, OR THE MAILING DATE OF THIS INTERVIEW SUMMARY FORM, WHICHEVER IS LATER, TO FILE A STATEMENT OF THE SUBSTANCE OF THE INTERVIEW. See Summary of Record of Interview requirements on reverse side or on attached sheet.

Examiner Note: You must sign this form unless it is an Attachment to a signed Office action.

 12/4/04
Examiner's signature, if required

Continuation of Substance of Interview including description of the general nature of what was agreed to if an agreement was reached, or any other comments: Discussion focused over the prior art references. The examiner suggests to include the following limitations: the nitrogen atoms do not reach the substrate; forming contact to the source and drain regions through the gate oxide after the step of introducing the nitrogen atoms into the gate oxide layer; and wherein the step of introducing N atoms and the step of depositing a CVD oxide film are conducted consecutively in a common processing chamber, without taking out said substrate into an atmospheric environment. However, the suggested limitations and arguments will require further consideration and search upon filing a response to the last Office action.